

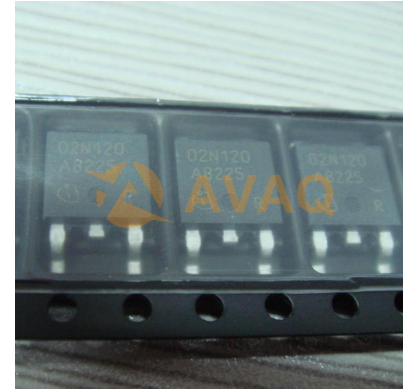
Trans IGBT Chip N-CH 1200V 6.2A 62mW 3-Pin(2+Tab) DPAK T/R

Manufacturer: [Infineon Technologies Corporation](#)

Package/Case: TO-252

Product Type: Thyristors

Lifecycle: LTB



Images are for reference only

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General Description

SGD02N120 is a part number for a power MOSFET (metal-oxide-semiconductor field-effect transistor) made by STMicroelectronics.

Key Features

- Drain-source voltage (VDS) rating of 1200V
- Continuous drain current (ID) rating of 2A
- Low on-state resistance (RDS(on)) of 2.5 ohms
- Fast switching speed
- TO-252 (DPAK) package

Application

- STW2N120 (also made by STMicroelectronics)
- FCPF02N60 (made by Fairchild Semiconductor)
- IRF610 (made by Infineon Technologies)



Recommended For You

SGW30N60HS

Infineon Technologies Corporation

TO-247

SGW50N60HS

Infineon Technologies Corporation

TO-247

SGB02N120

Infineon Technologies Corporation

TO-263

SGW30N60

Infineon Technologies Corporation

TO-247

SGP30N60

Infineon Technologies Corporation

PG-TO220-3

SGB10N60A

Infineon Technologies Corporation

TO-263

SGW25N120

Infineon Technologies Corporation

TO-247

SGW15N120

Infineon Technologies Corporation

TO-247

SGP07N120

Infineon Technologies Corporation

TO-220

SGP20N60

Infineon Technologies Corporation

TO-220

SGB30N60

Infineon Technologies Corporation

TO-263

SGP10N60A

Infineon Technologies Corporation

PG-TO220-3

SGW15N60FKSA1

Infineon Technologies Corporation

BGA

SGB20N60ATMA1

Infineon Technologies Corporation

BGA

SGP30N60XKSA1

Infineon Technologies Corporation

BGA